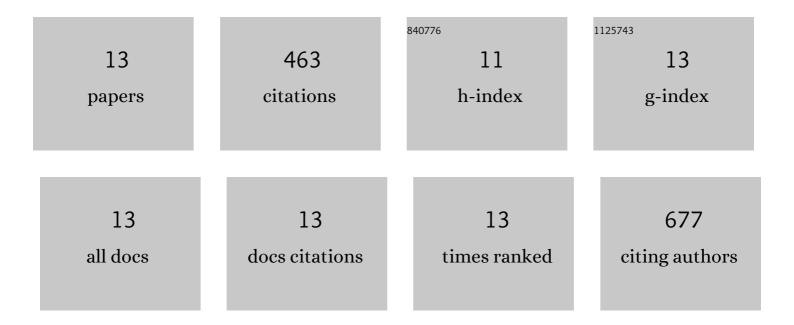
## Ebrahim Najafi

List of Publications by Year in descending order

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FRDAHIM NAIAFI

#	Article	IF	CITATIONS
1	Four-dimensional imaging of carrier interface dynamics in p-n junctions. Science, 2015, 347, 164-167.	12.6	90
2	Super-diffusion of excited carriers in semiconductors. Nature Communications, 2017, 8, 15177.	12.8	60
3	Spatial-Temporal Imaging of Anisotropic Photocarrier Dynamics in Black Phosphorus. Nano Letters, 2017, 17, 3675-3680.	9.1	56
4	Photo-excited hot carrier dynamics in hydrogenated amorphous silicon imaged by 4D electron microscopy. Nature Nanotechnology, 2017, 12, 871-876.	31.5	48
5	Polarization Dependence of the C 1s Xâ€ray Absorption Spectra of Individual Multiâ€Walled Carbon Nanotubes. Small, 2008, 4, 2279-2285.	10.0	46
6	Scanning ultrafast electron microscopy: A novel technique to probe photocarrier dynamics with high spatial and temporal resolutions. Materials Today Physics, 2017, 2, 46-53.	6.0	37
7	Measuring Point Defect Density in Individual Carbon Nanotubes Using Polarization-Dependent X-ray Microscopy. ACS Nano, 2010, 4, 4431-4436.	14.6	36
8	Characterization of Single-Walled Carbon Nanotubes by Scanning Transmission X-ray Spectromicroscopy: Purification, Order and Dodecyl Functionalization. Journal of the American Chemical Society, 2010, 132, 9020-9029.	13.7	30
9	Imaging surface acoustic wave dynamics in semiconducting polymers by scanning ultrafast electron microscopy. Ultramicroscopy, 2018, 184, 46-50.	1.9	18
10	Metallic and Semiconducting Single-Walled Carbon Nanotubes: Differentiating Individual SWCNTs by Their Carbon 1s Spectra. ACS Nano, 2012, 6, 10965-10972.	14.6	17
11	Mapping defects in a carbon nanotube by momentum transfer dependent electron energy loss spectromicroscopy. Ultramicroscopy, 2012, 113, 158-164.	1.9	17
12	Ultrafast imaging of surface-exclusive carrier dynamics in silicon. Journal of Applied Physics, 2019, 125,	2.5	6
13	Carrier density oscillation in the photoexcited semiconductor. Journal Physics D: Applied Physics, 2021, 54, 125102.	2.8	2